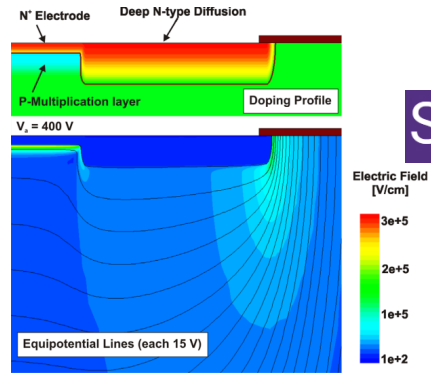
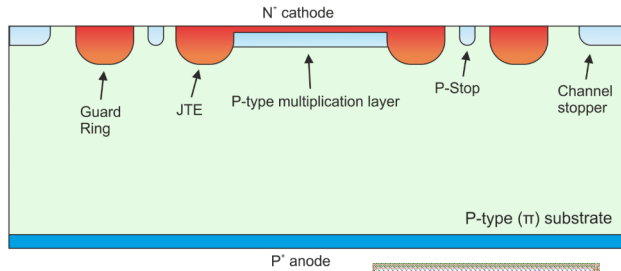


# LGAD development at the IMB-CNM

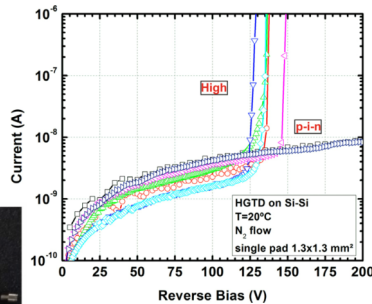
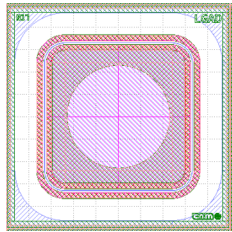
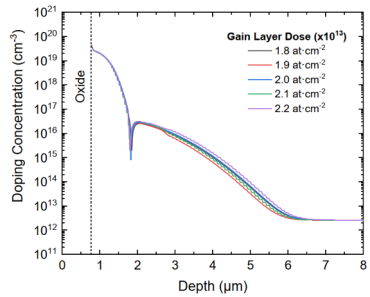
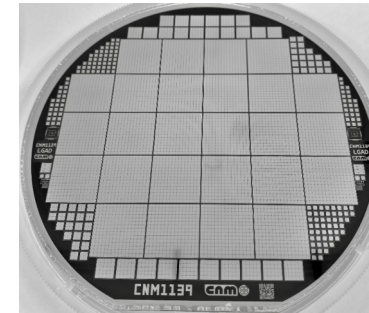
P. Fernandez-Martinez, N. Moffat J. Villegas,  
M.Manojlovic, S.Hidalgo, G.Pellegrini

- We can contribute to all the sensor R&D steps



**SYNOPSYS**  
Synopsys TCAD

<https://www.imb-cnm.csic.es/en>  
<https://rdg.imb-cnm.csic.es/>



Technological Design

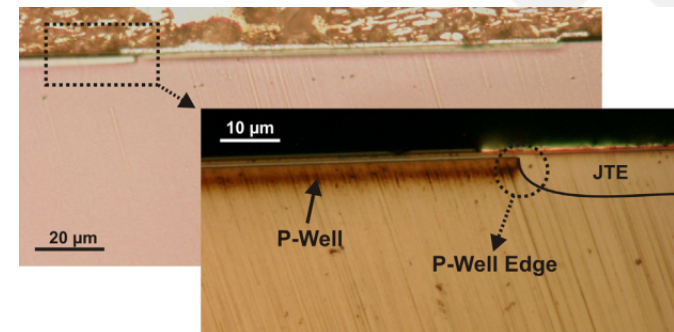
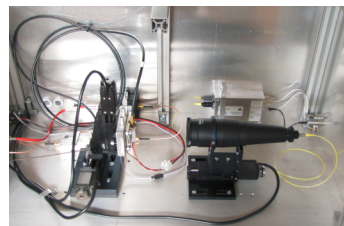
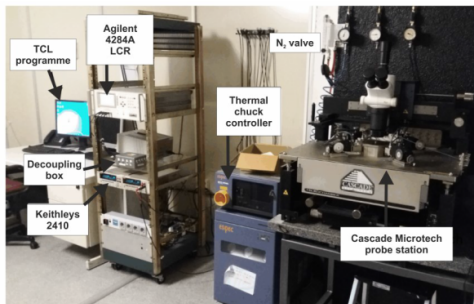
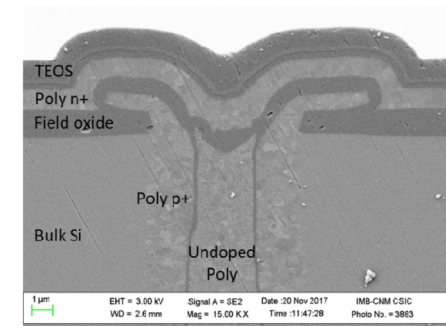
Simulation

Fabrication

Sensor R&D

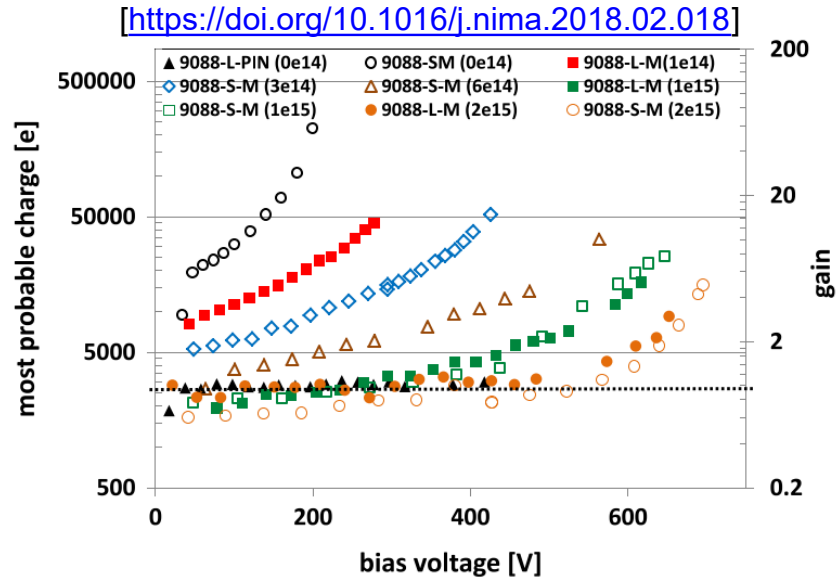
Characterization

Inspection

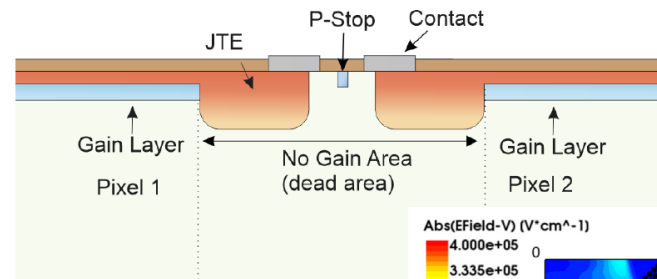


1st DRD3 week on Solid State Detectors R&D

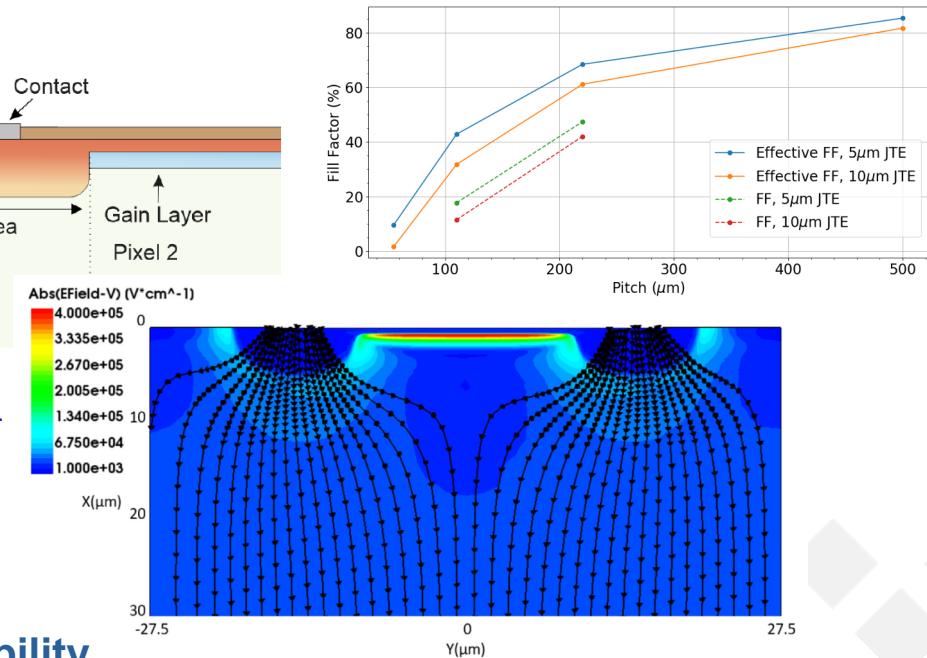
- a) **Radiation Hardness:** Gain decreases with fluence
- Serious challenge for HL-LHC applications and beyond



- b) **Fill factor:** Termination (non-gain area) dominates for small pixels
- Need to account for drift to JTE
  - Good timing reconstruction requires homogeneous weighting field



<https://doi.org/10.1016/j.nima.2021.165746>



- c) Other certainly non-minor challenges: **Fabrication Yield** and **Device Reliability**

- Compromising many-pixel structures, large devices and even moderate productions

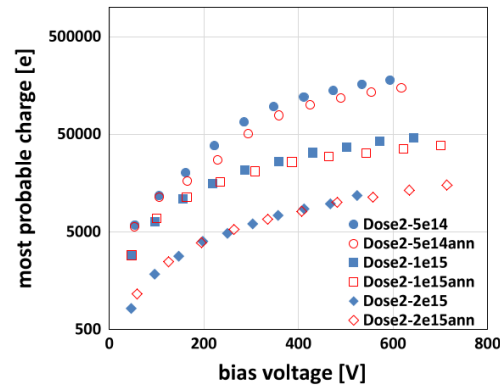
- d) Classic design is not optimal for **low penetrating particles** (lower efficiency, lower gain)

- Many attractive applications in this category: low energy protons, soft X-rays, UV photons and beyond

## What we have tried

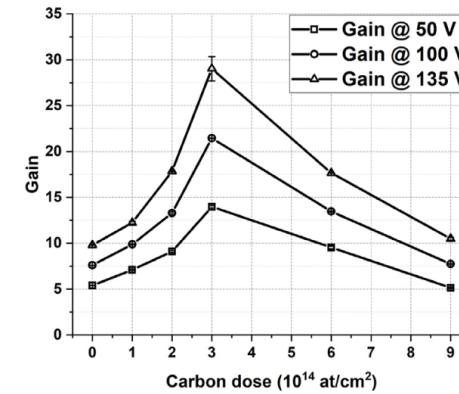
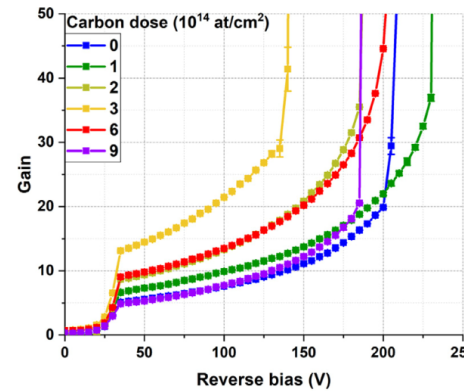
- Replace Boron with Gallium

<https://doi.org/10.1016/j.nima.2018.04.060>



- Carbon enrichment

<https://doi.org/10.1016/j.nima.2024.169424>



## Further steps:

- Partial activation of the gain implant (on going)

RD50 funding request

- Date: 15.11.2023 -

Title of project: **Partial Activation of Boron to enhance the radiation tolerance of the gain implant – PAB**

Contact person: V. Sola  
Torino University and INFN  
+39 011 670 7338  
[valentina.sola@to.infn.it](mailto:valentina.sola@to.infn.it)

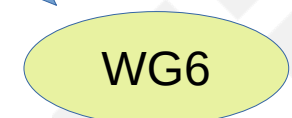
- Links with other WG (or projects)



- 3D sensors for timing

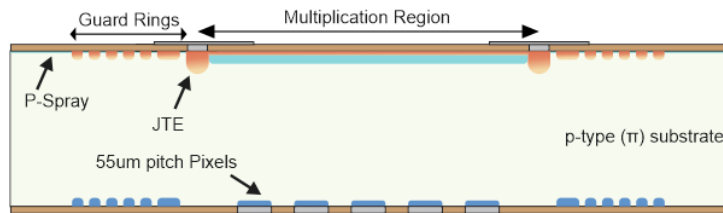


- Radiation hardness techniques



- Other substrates (SiC, etc.)

## Inverse LGAD (iLGAD)



### Readout ASIC

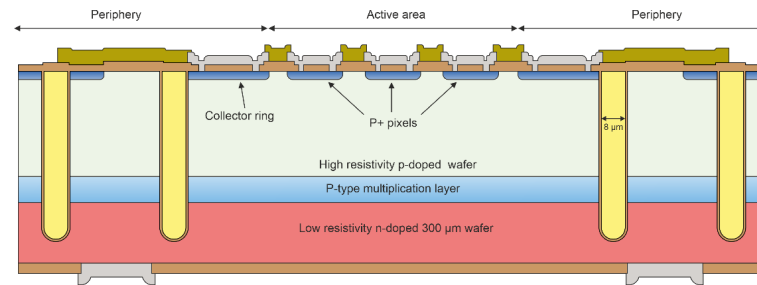
- Ohmic contact segmented
- Multiplication region extends over all the device

#### Cons

- Double side processing
- Backside sensitive to scratches
- Needs to be fully depleted

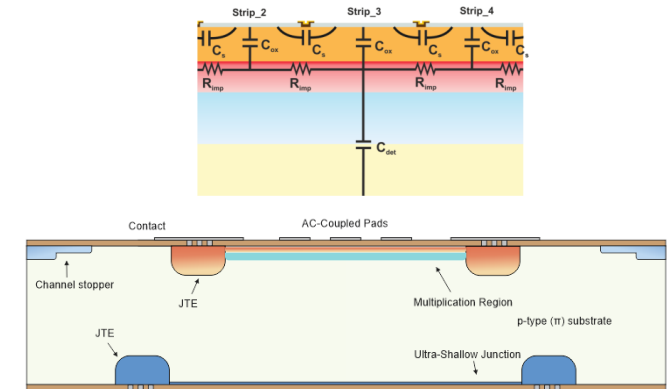
doi:10.1088/1748-0221/11/12/C12039  
<https://doi.org/10.1016/j.nima.2019.162545>

## Trench Isolated iLGAD

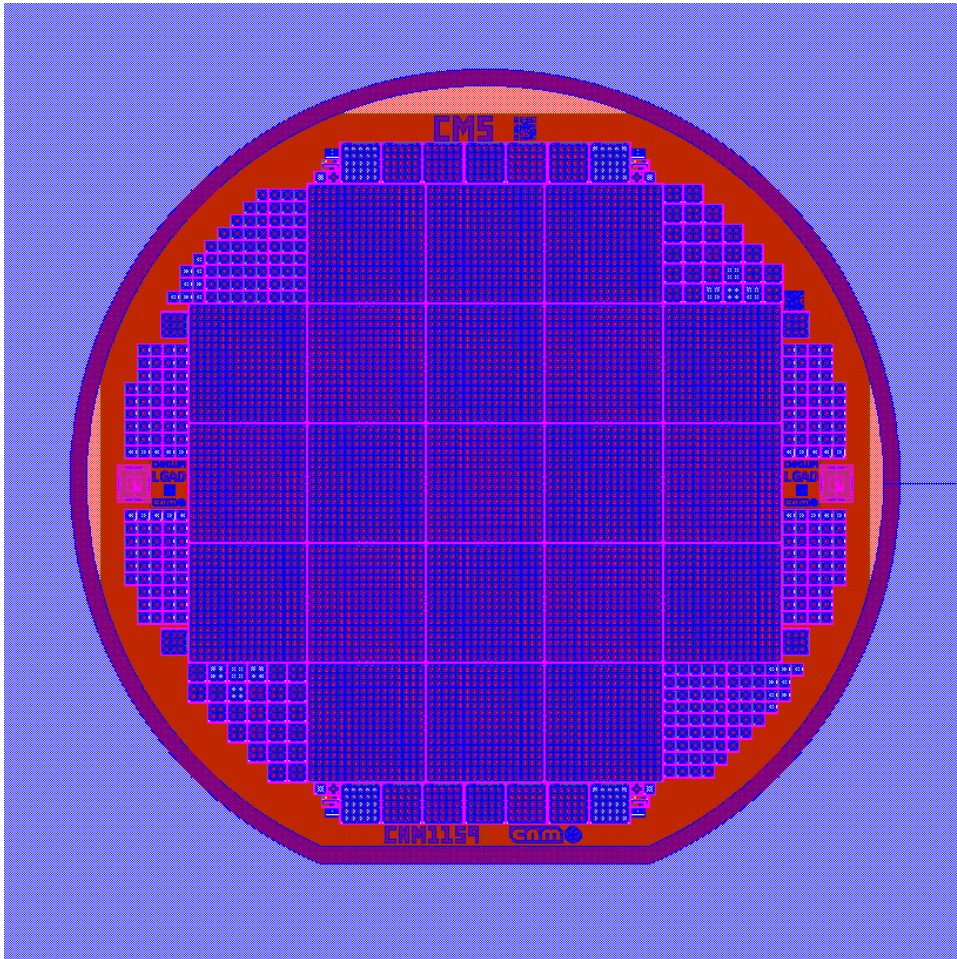


- Fully isolated multiplication region
- **Single-side** and **50% less** fabrication steps.
- **Higher voltages**
- **Slim-edge technology.**
- Optimization of the **multiplication layer is independent of charge collection and cross-talk at the electrodes.**

## AC LGAD



- Pad segmentation replaced into **metal segmentation**
- The signal is AC-coupled into the metal pads by another continuous sheet of coupling oxide.



Latest mask set with 16x16 pixel devices + single pad LGADs

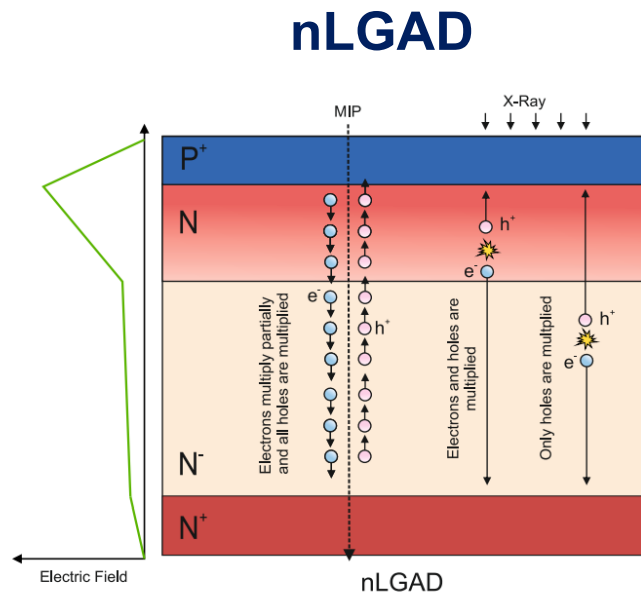
- We have experienced fabrication issues with a clear impact on the yield of our technologies
  - In the latests runs, this might be partially attributable to the major upgrade of the CR equipments (but not only)
  - Many different technologies, broad variation of parameters → Not helping to standardize processes



Dedicated runs to stabilize our technologies

- Looking for higher reliability (same performance and characteristics, among *and within* devices)
  - Increased number of inspection steps
  - Careful study of the metallization and passivation
  - Use of deep multiplication layer (on going)

- Many applications beyond high-energy physics experiments...



### proton LGAD

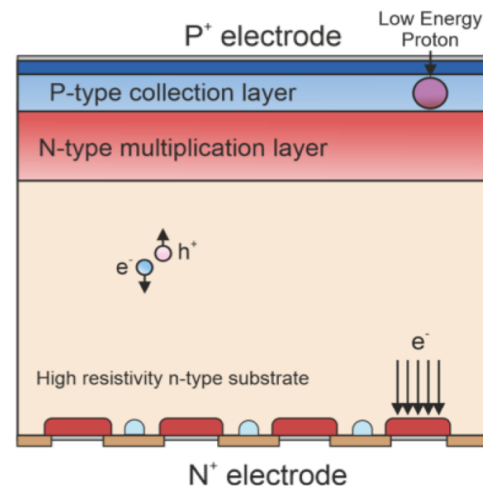


Fig. 1. Cross section of the nLGAD device

- Specifically designed to enhance low penetrating radiation detection (soft Xray, UV, etc.)
- Check previous talk [Fernandez DRD3]

J. Villegas - TREDI2024

<https://doi.org/10.1016/j.nima.2023.168377>

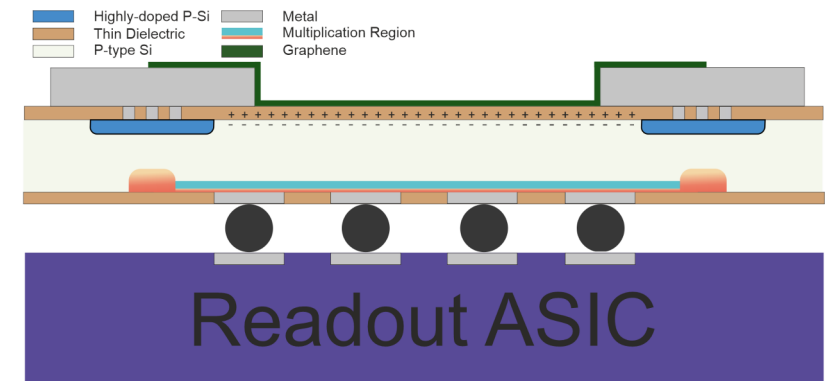
- Version of nLGAD tailored for low energy proton detection
- Includes a collection layer with lower dose below the P<sup>+</sup> electrode

[10.1109/CDE52135.2021.9455752](https://doi.org/10.1109/CDE52135.2021.9455752)

<https://doi.org/10.1016/j.nima.2022.167220>

Patent: WO2022063852 A1

### AC LGAD – Graphene on Silicon



- Absorption layer (the 35um Si) and bulk Si (the 300um Si)
- Graphene placed on top of thin dielectric (3nm) in electrical contact with metal

[10.1109/NANO54668.2022.9928637](https://doi.org/10.1109/NANO54668.2022.9928637)

## We were there from the beginning...



Nuclear Instruments and Methods in  
Physics Research Section A: Accelerators,  
Spectrometers, Detectors and Associated  
Equipment

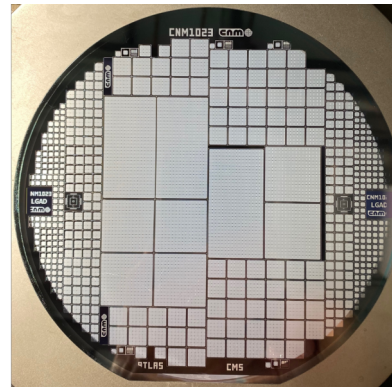


Volume 765, 21 November 2014, Pages 12-16

Technology developments and first  
measurements of Low Gain Avalanche  
Detectors (LGAD) for high energy  
physics applications

G. Pellegrini<sup>a</sup>, P. Fernández-Martínez<sup>a</sup>, M. Baselga<sup>a</sup>, C. Fleita<sup>a</sup>, D. Flores<sup>a</sup>,  
V. Greco<sup>a</sup>, S. Hidalgo<sup>a</sup>, I. Mandić<sup>b</sup>, G. Kramberger<sup>b</sup>, D. Quirion<sup>a</sup>, M. Ullan<sup>a</sup>

## We took part in the advances...



We are eager to keep enjoying the fun...

# DRD3

*Foot Note: We need a logo...*





# Thanks for your attention

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Barcelona · Spain



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Thanks for your  
attention!

- Equipment:

- Thermal processes, CVD and ALD
- Ion Implantation
- PVD and Metallisation (Sputtering and Evaporators)
- Optical Lithography:
  - Proximity Aligners: single and double side
  - Steppers: g-line and i-line
  - Direct laser writing
- Nano-lithography (e-beam, NIL, FIB and AFM)
- Dry etching
- Wet and dry micromachining
- Wet etching and cleaning
- On-line test
- Conventional and advanced packaging
- Electrical characterization

